

# Assocâ€Prof Hannes Raebiger

## List of Publications by Year in descending order

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53

papers

1,897

citations

471509

17

h-index

276875

41

g-index

54

all docs

54

docs citations

54

times ranked

2942

citing authors

#	ARTICLE	IF	CITATIONS
1	Parallel Alignment of Methylammonium Cations in an Orthorhombic $\text{CH}_{3}\text{NH}_3\text{PbCl}_3$ Single Crystal Observed by Polarized Micro-Raman Scattering Spectroscopy. <i>Chemistry of Materials</i> , 2022, 34, 2972-2980.	6.7	3
2	Electronic and magnetic properties of carbide MXenes—the role of electron correlations. <i>Materials Today Advances</i> , 2021, 9, 100118.	5.2	35
3	MXene Phase with $\text{C}_3$ Structure Unit: A Family of 2D Electrides. <i>Advanced Functional Materials</i> , 2021, 31, 2100009.	14.9	13
4	2D Electrides: MXene Phase with $\text{C}_3$ Structure Unit: A Family of 2D Electrides (Adv. Funct.) Tj ETQq0 0.0 rgBT /Overlock 10	14.9	10
5	Normalization of exact quasiparticle wave functions in the Green's function method guaranteed by the Ward identity. <i>Physical Review B</i> , 2021, 104, .	3.2	3
6	Strain Engineering to Release Trapped Hole Carriers in p-Type Haeckelite GaN. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5257-5264.	4.3	1
7	Modulation of the optical absorption edge of $\mu$ - and $\text{Ga}_2\text{O}_3$ due to Co impurities caused by band structure changes: Work function measurements and first-principle calculations. <i>Journal of Applied Physics</i> , 2020, 127, 065701.	2.5	4
8	Electronic mechanism for resistive switching in metal/insulator/metal nanodevices. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 295302.	2.8	1
9	Carrier mediated ferromagnetism in $\text{Ga}_2\text{O}_3:\text{Cr}$ . <i>Applied Physics Express</i> , 2020, 13, 021002.	2.4	6
10	Reply to Correspondence on “Core Electron Topologies in Chemical Compounds: Case Study of Carbon versus Silicon”. <i>Angewandte Chemie - International Edition</i> , 2019, 58, 10408-10409.	13.8	0
11	Reply to Correspondence on “Core Electron Topologies in Chemical Compounds: Case Study of Carbon versus Silicon”. <i>Angewandte Chemie</i> , 2019, 131, 10516-10517.	2.0	0
12	First principles methods for defects: state-of-the-art and emerging approaches. , 2019, , 289-343.		2
13	Core Electron Topologies in Chemical Compounds: Case Study of Carbon versus Silicon. <i>Angewandte Chemie</i> , 2018, 130, 7130-7136.	2.0	6
14	Core Electron Topologies in Chemical Compounds: Case Study of Carbon versus Silicon. <i>Angewandte Chemie - International Edition</i> , 2018, 57, 7012-7018.	13.8	6
15	Frontispiz: Core Electron Topologies in Chemical Compounds: Case Study of Carbon versus Silicon. <i>Angewandte Chemie</i> , 2018, 130, .	2.0	0
16	Frontispiece: Core Electron Topologies in Chemical Compounds: Case Study of Carbon versus Silicon. <i>Angewandte Chemie - International Edition</i> , 2018, 57, .	13.8	0
17	Control of hole localization in magnetic semiconductors by axial strain. <i>Physical Review Materials</i> , 2018, 2, .	2.4	7
18	Defect-Induced Vibration Modes of $\text{ArMoS}_2$ Irradiated $\text{MoS}_2$ . <i>Physical Review Applied</i> , 2017, 7, .	3.8	58

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19	Critical metal-insulator transition due to nuclear quantum effects in Mn-doped GaAs. Physical Review B, 2016, 94, .	3.2	7
20	Charge storage in oxygen deficient phases of TiO <sub>2</sub> : defect Physics without defects. Scientific Reports, 2016, 6, 28871.	3.3	48
21	Positron Binding Properties of Glycine and Its Aqueous Complexes. Journal of Physical Chemistry A, 2016, 120, 4037-4042.	2.5	14
22	Phonon Properties of Few-Layer Crystals of Quasi-One-Dimensional ZrS <sub>3</sub> and ZrSe <sub>3</sub> . Journal of Physical Chemistry C, 2016, 120, 4653-4659.	3.1	41
23	Term rules for simple metal clusters. Scientific Reports, 2015, 5, 15760.	3.3	4
24	Pairwise chemical interactions of charged transition-metal impurities in insulators. Physical Review B, 2014, 90, .	3.2	2
25	Schottky Barrier Formation and Strain at the (011) $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline">\times mml:mrow \times mml:mi>GdN\langle mml:mi>\times mml:mo/\langle /mml:mo>\times mml:mi>GaN\langle mml:mi>\times /mml:mrow^3:8\langle /mml:math\rangle$ Interface from First Principles. Physical Review Applied, 2014, 2, .	8	8
26	Direct d-d interactions among transition metal impurities in III-V semiconductors. Applied Physics Express, 2014, 7, 023004.	2.4	3
27	Molecular Motion Induced by Multivibronic Excitation on Semiconductor Surface. Journal of Physical Chemistry C, 2014, 118, 1554-1559.	3.1	5
28	Control of defect binding and magnetic interaction energies in dilute magnetic semiconductors by charge state manipulation. Journal of Applied Physics, 2014, 115, 012008.	2.5	9
29	Magnetic Properties and Stability of Quasi-One-Dimensional Cr Chains Embedded in (Zn,Cr)Te. Applied Physics Express, 2013, 6, 073006.	2.4	2
30	Interfacial Stress and Thermal Expansion Effects for PL Spectra in AlGaN-GaN MQW. AIP Conference Proceedings, 2011, , .	0.4	0
31	Multiple exchange interactions induced by Jahn-Teller distortions in dilute magnetic semiconductors. Physical Review B, 2011, 84, .	3.2	5
32	Theory of defect complexes in insulators. Physical Review B, 2010, 82, .	3.2	8
33	Oxidation numbers as Social Security Numbers: Are they predictive or postdictive?. Nature Precedings, 2009, , .	0.1	2
34	Electronic structure, donor and acceptor transitions, and magnetism of $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline">\times mml:mrow \times mml:mn>3\langle /mml:mn>\times mml:mi>d\langle /mml:mi>\times /mml:math>$ impurities in $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline">\times mml:mrow \times mml:msub>\langle mml:mrow>\langle mml:mtext>In\langle /mml:mtext>\times /mml:mrow>\times mml:mn>2\langle /mml:mn>\times /mml:math>$ ZnO. Physical Review B, 2009, 79, .	3.2	104
35	Charge self-regulation upon changing the oxidation state of transition metals in insulators. Nature, 2008, 453, 763-766.	27.8	241
36	Relative stability, electronic structure, and magnetism of MnN and (Ga,Mn)N alloys. Physical Review B, 2008, 78, .	3.2	39

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37	Control of Ferromagnetism via Electron Doping in $\text{In}_2\text{O}_3$ . <i>Physical Review Letters</i> , 2007, 99, 167203. Magnetic interactions of $\text{Cr}^{3+}$ in $\text{ZnO}$ . <i>Physical Review Letters</i> , 2007, 99, 167204.	7.8	70
38	Electronic structure of $\text{Co}_{1-x}\text{Mn}_x\text{O}$ . <i>Physical Review Letters</i> , 2007, 99, 167205.	7.8	139
39	Structural and magnetic properties of $(\text{Ga},\text{Mn})\text{N}$ from first principles. <i>Physical Review B</i> , 2007, 75, .	3.2	29
40	Impurity Clustering and Ferromagnetic Interactions that are not Carrier Induced in Dilute Magnetic Semiconductors: The Case of $\text{Cu}_2\text{O}-\text{Co}$ . <i>Physical Review Letters</i> , 2007, 99, 167203. Origins of the band-like behavior of $\text{Cu}_{1-x}\text{Mn}_x\text{O}$ .	7.8	43
41	Electronic structure of $\text{Co}_{1-x}\text{Mn}_x\text{O}$ . <i>Physical Review Letters</i> , 2007, 99, 167205.	3.2	456
42	Effects of Mn clustering on ferromagnetism in $(\text{Ga},\text{Mn})\text{As}$ . <i>Physica B: Condensed Matter</i> , 2006, 376-377, 643-646.	2.7	4
43	A multiscale study of ferromagnetism in clustered $(\text{Ga},\text{Mn})\text{N}$ . <i>Journal of Physics Condensed Matter</i> , 2006, 18, 1561-1567.	1.8	12
44	Ferromagnetism and its evolution during long-term annealing in $(\text{Ga},\text{Mn})\text{As}$ . <i>Physical Review B</i> , 2006, 74, .	3.2	10
45	Diffusion and clustering of substitutional Mn in $(\text{Ga},\text{Mn})\text{As}$ . <i>Applied Physics Letters</i> , 2006, 89, 012505.	3.3	25
46	High Curie temperatures in $(\text{Ga},\text{Mn})\text{N}$ from Mn clustering. <i>Applied Physics Letters</i> , 2006, 88, 122501.	3.3	37
47	Clustering of Mn in $(\text{Ga},\text{Mn})\text{As}$ . <i>Journal of Magnetism and Magnetic Materials</i> , 2005, 290-291, 1398-1401.	2.3	14
48	Electronic and magnetic properties of substitutional Mn clusters in $(\text{Ga},\text{Mn})\text{As}$ . <i>Physical Review B</i> , 2005, 72, .	3.2	57
49	Intrinsic hole localization mechanism in magnetic semiconductors. <i>Journal of Physics Condensed Matter</i> , 2004, 16, L457-L462.	1.8	64
50	Spontaneous magnetization of aluminum nanowires deposited on the $\text{NaCl}(100)$ surface. <i>Physical Review B</i> , 2002, 66, .	3.2	31
51	Electronic structure and prediction of magnetism in metallic nanowires. <i>Journal of Magnetism and Magnetic Materials</i> , 2002, 249, 193-199.	2.3	16
52	The quest for dilute ferromagnetism in semiconductors: Guides and misguides by theory. <i>Physics Magazine</i> , 0, 3, .	0.1	200
53	Electronic Structures of Group III-V Element Haecelite Compounds: A Novel Family of Semiconductors, Dirac Semimetals, and Topological Insulators. <i>Advanced Functional Materials</i> , 0, , 2110930.	14.9	3